

Development and application of a massively parallel KKR Green function method for large scale systems

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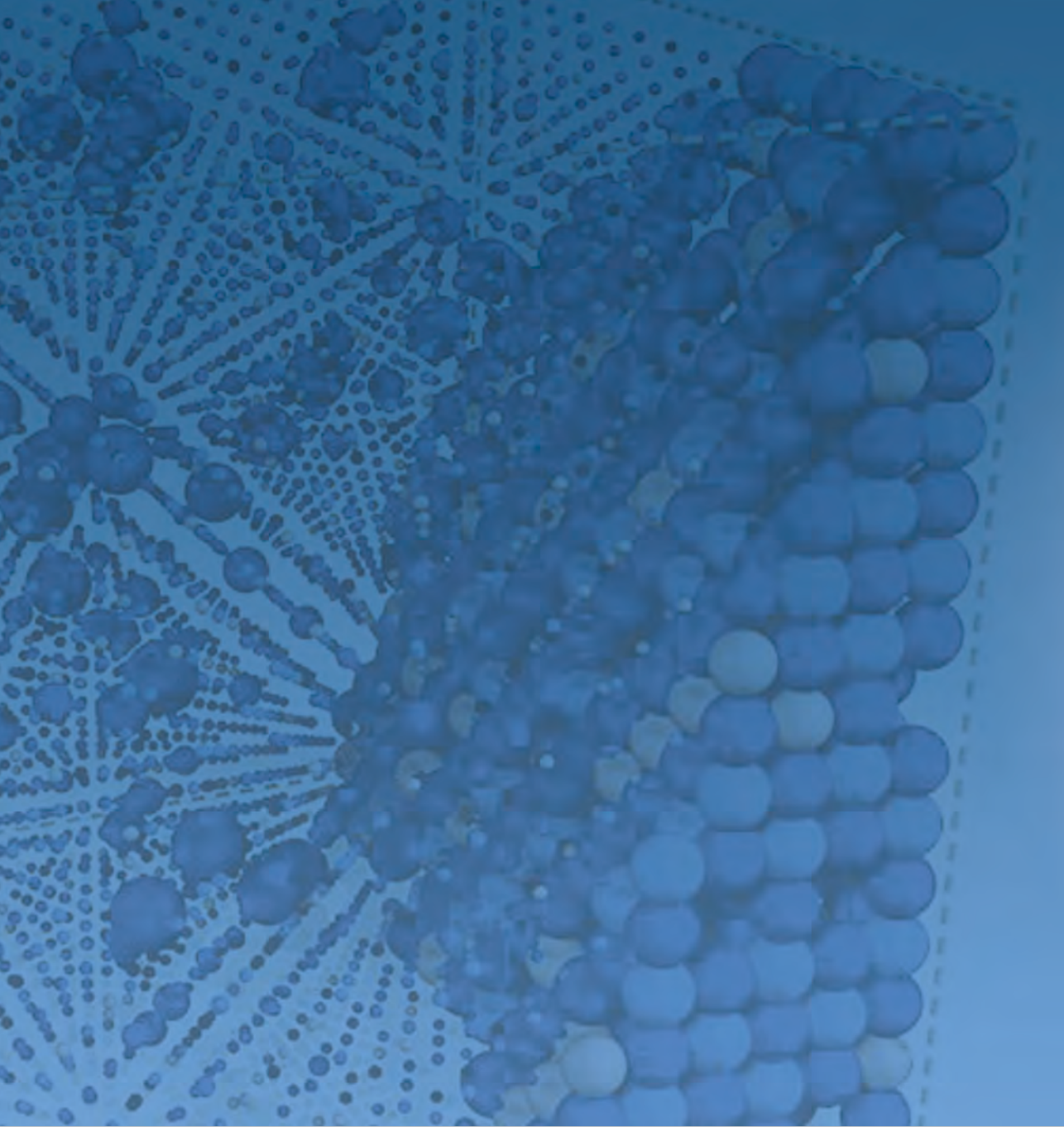
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